

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a ITO220 plastic package intended for use in applications requiring very high inrush current capability, high thermal cycling performance and high junction temperature capability ($T_{j(max)} = 150\text{ °C}$).

2. Features and benefits

- High junction operating temperature capability ($T_{j(max)} = 150\text{ °C}$)
- Very high current surge capability
- Planar passivated for voltage ruggedness and reliability
- High thermal cycling performance
- High voltage capability

3. Applications

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control
- Uninterruptible Power Supply (UPS)
- Solid State Relay (SSR)
- Traction battery charging

4. Quick reference data

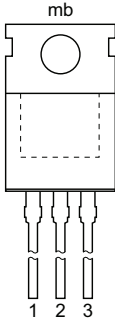

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{DRM}	repetitive peak off-state voltage			800	V
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 112\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3		30	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 10\text{ ms}$; Fig 4 ; Fig 5		400	A
		half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 8.3\text{ ms}$		440	A
T_j	operating junction temperature			150	°C

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 7		6	-	15	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 9		-	-	60	mA
V_T	on-state voltage	$I_T = 30\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10		-	1.10	1.30	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_j = 150\text{ °C}$; exponential waveform; gate open circuit		1000	-	-	V/ μs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	A	anode		
3	G	gate		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
TYN30Y-800TN	IITO220	TYN30Y-800TNQ	Tube	50	SOT78D	10-July-2007

7. Marking

Table 4. Marking codes

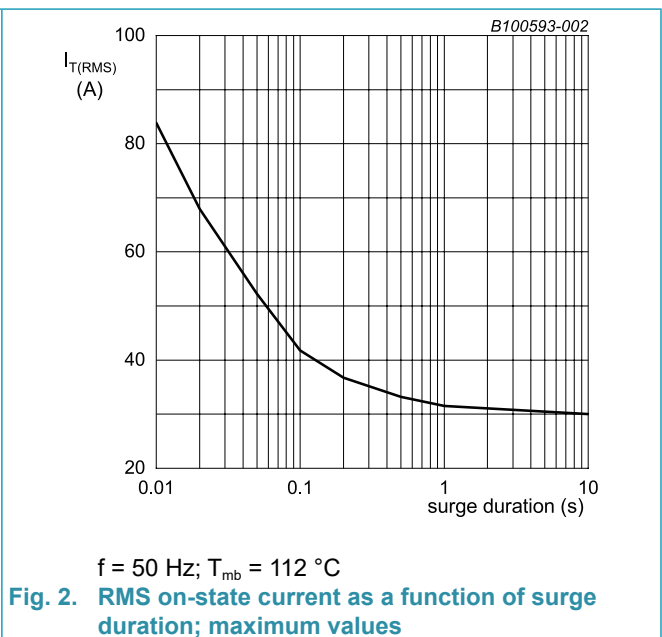
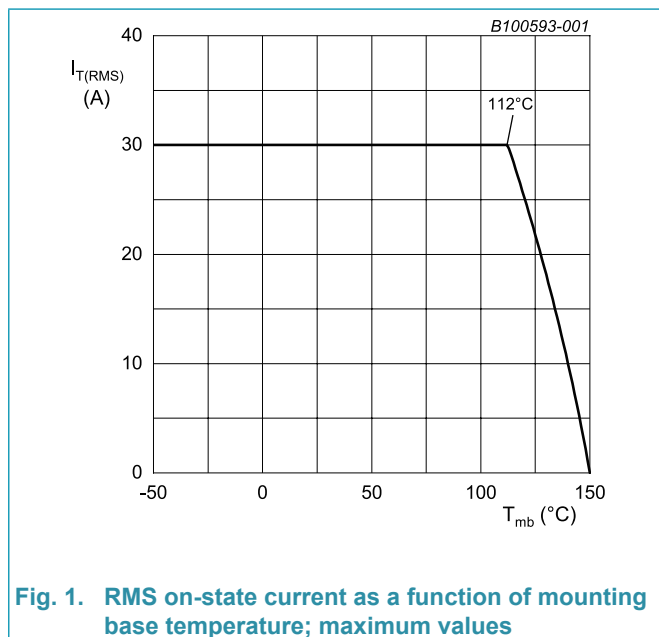
Type number	Marking codes
TYN30Y-800TN	TYN30Y 800TN

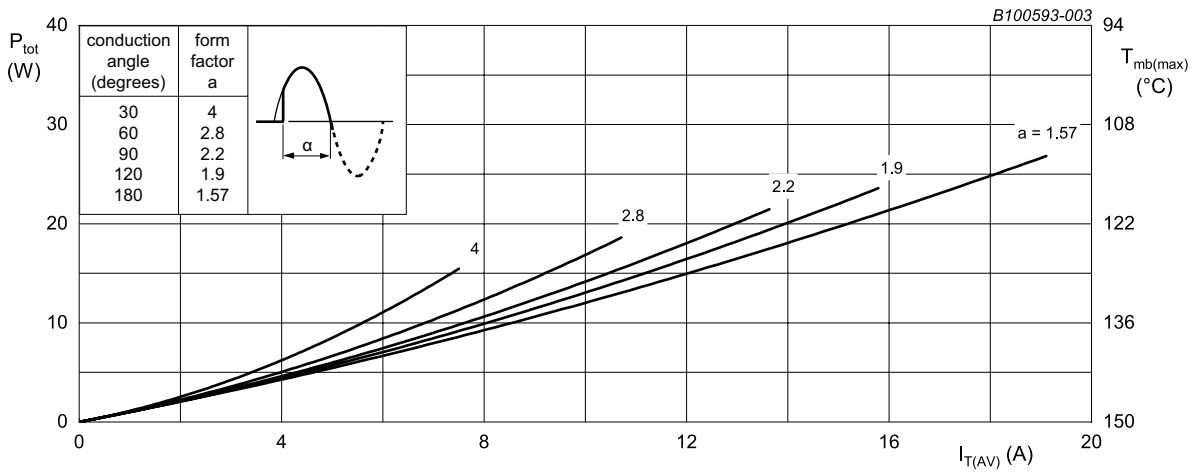
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

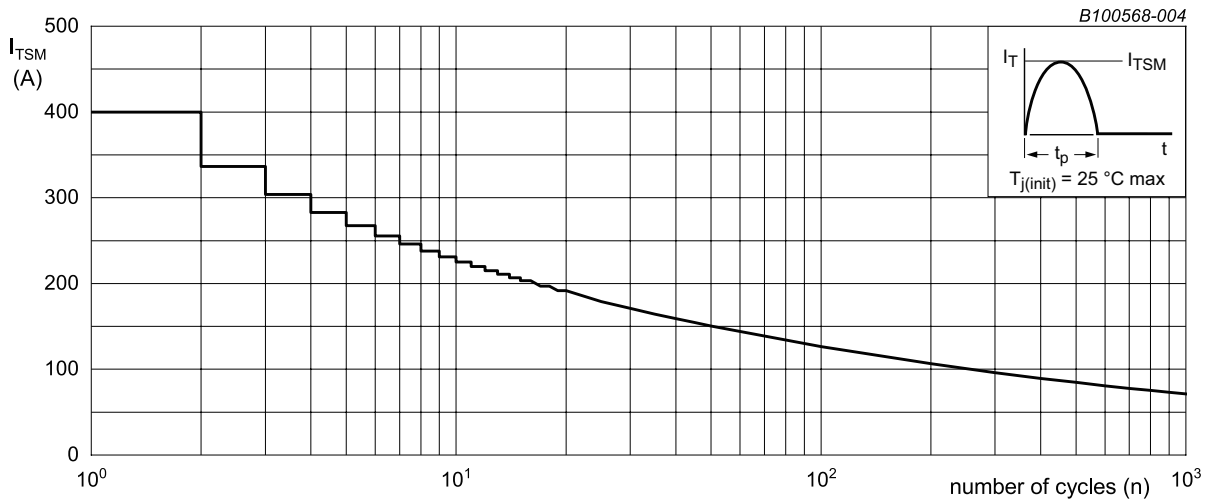
Symbol	Parameter	Conditions	Notes	Values	Unit
V_{DRM}	repetitive peak off-state voltage			800	V
V_{RRM}	repetitive peak reverse voltage			800	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 112\text{ }^{\circ}\text{C}$;		19	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 112\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3		30	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$; Fig 4 ; Fig 5		400	A
		half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 8.3\text{ ms}$		440	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse		800	A^2s
di_T/dt	rate of rise of on-state current	$I_G = 30\text{ mA}$		500	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current			5	A
V_{GM}	peak gate voltage			5	V
V_{RGM}	peak reverse gate voltage			7	V
P_{GM}	peak gate power			20	W
$P_{G(AV)}$	average gate power	over any 20 ms period		0.5	W
T_{stg}	storage temperature			-40 to 150	$^{\circ}\text{C}$
T_j	operating junction temperature			150	$^{\circ}\text{C}$





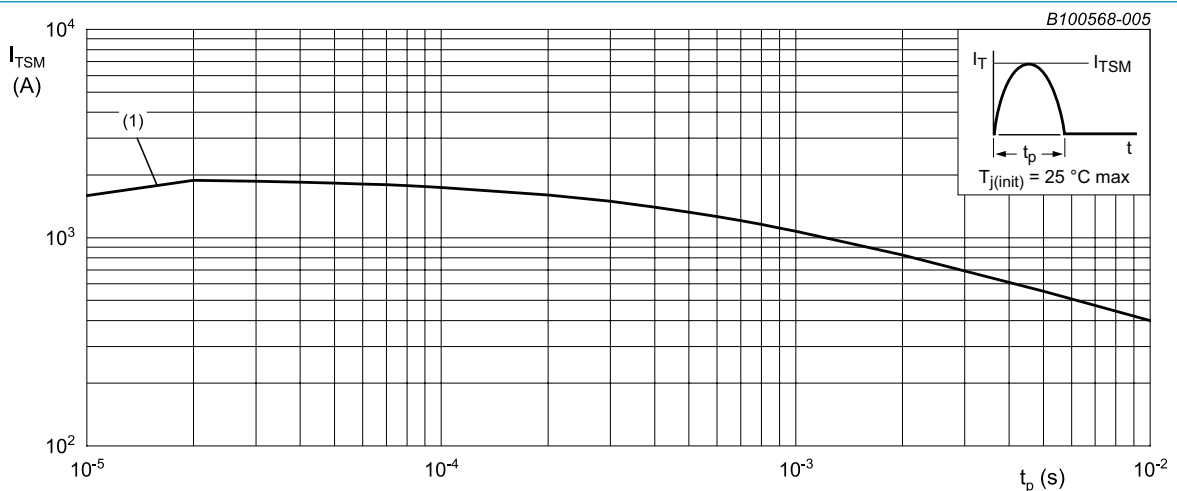
α = conduction angle
 a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 10$ ms
 (1) di_T/dt limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig 6		-	-	1.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	60	-	K/W

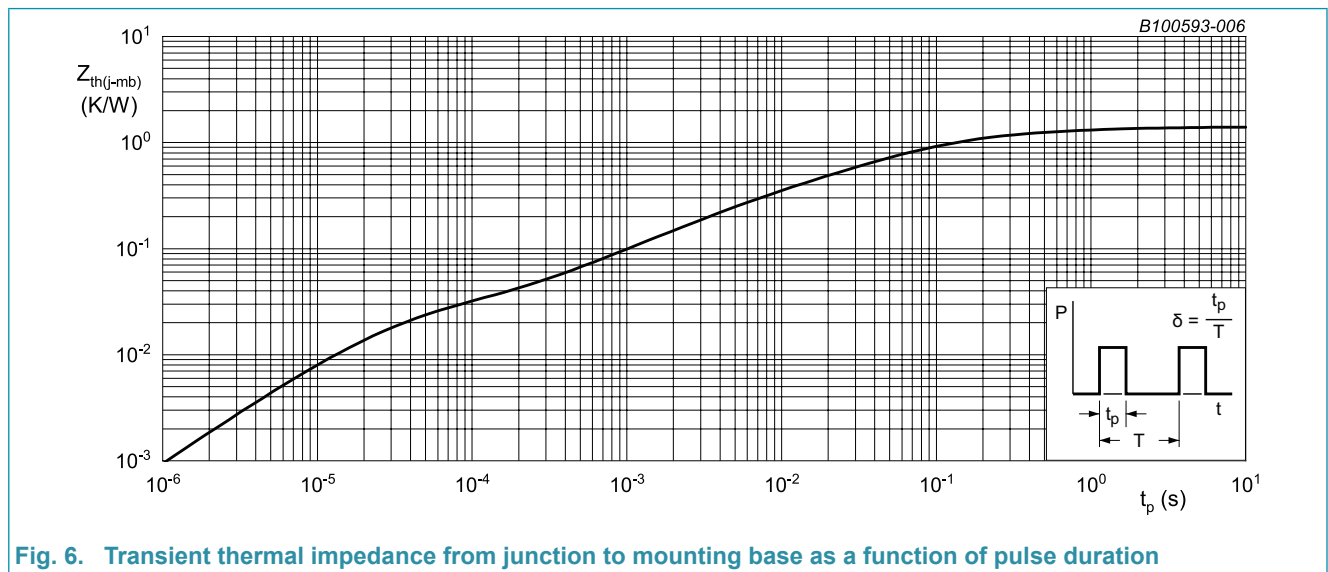


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Isolation characteristics

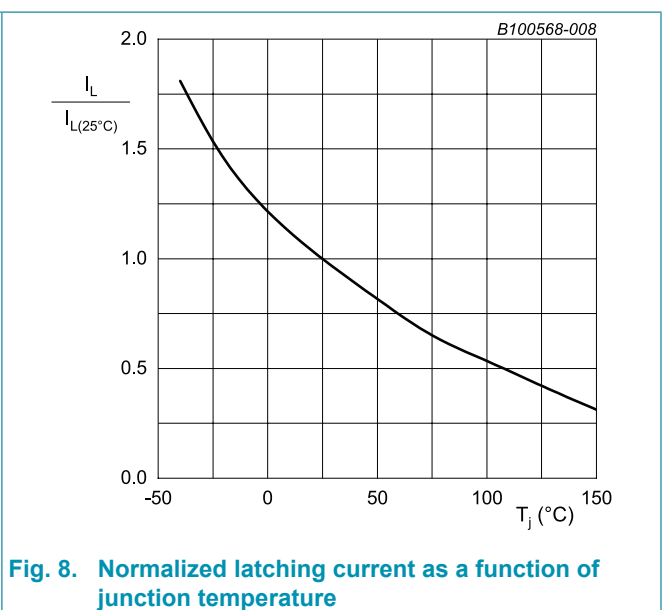
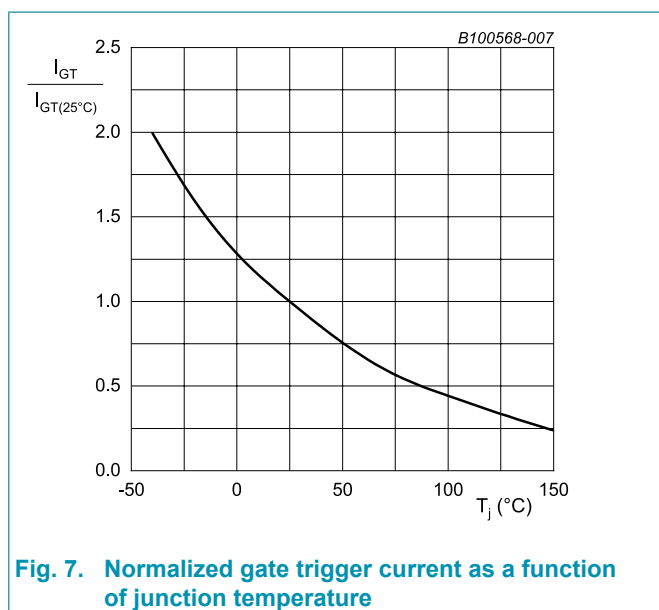
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free		-	-	2500	V
C_{isol}	isolation capacitance	from cathode to external heatsink		-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C}$; Fig. 7		6	-	15	mA
I_L	latching current	$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C}$; Fig. 8		-	-	80	mA
I_H	holding current	$V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C}$; Fig. 9		-	-	60	mA
V_T	on-state voltage	$I_T = 30\text{ A}; T_j = 25\text{ }^\circ\text{C}$; Fig. 10		-	1.10	1.30	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C}$; Fig. 11		-	0.6	1	V
		$V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_j = 150\text{ }^\circ\text{C}$		0.25	0.4	-	V
I_D	off-state current	$V_D = 800\text{ V}; T_j = 25\text{ }^\circ\text{C}$		-	-	10	μA
		$V_D = 800\text{ V}; T_j = 150\text{ }^\circ\text{C}$		-	-	1	mA
I_R	reverse current	$V_R = 800\text{ V}; T_j = 25\text{ }^\circ\text{C}$		-	-	10	μA
		$V_R = 800\text{ V}; T_j = 150\text{ }^\circ\text{C}$		-	-	1	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}; T_j = 150\text{ }^\circ\text{C}$; exponential waveform; gate open circuit		1000	-	-	V/ μs
		$V_{DM} = 536\text{ V}; T_j = 150\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		500	-	-	V/ μs
t_{gt}	gate-controlled turn-on time	$I_{TM} = 30\text{ A}; V_D = 800\text{ V}; I_G = 100\text{ mA}$; $dI_G/dt = 5\text{ A}/\mu\text{s}$; $T_j = 25\text{ }^\circ\text{C}$		-	2	-	μs
t_q	commutated turn-off time	$V_{DM} = 536\text{ V}; T_j = 150\text{ }^\circ\text{C}$; $I_{TM} = 30\text{ A}$; $V_R = 25\text{ V}$; $dI_T/dt = 30\text{ A}/\mu\text{s}$; $dV_D/dt = 50\text{ V}/\mu\text{s}$		-	70	-	μs



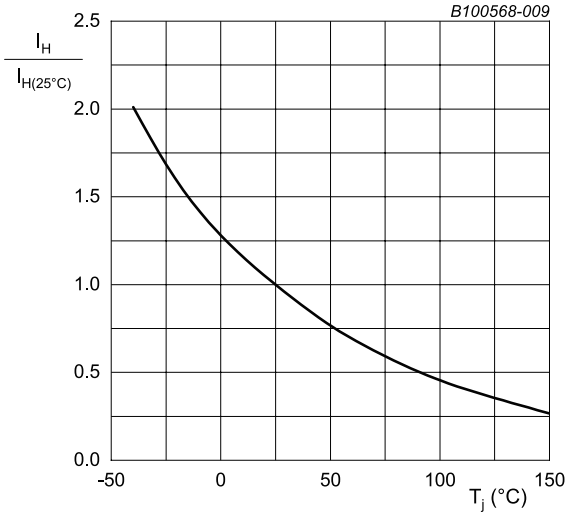
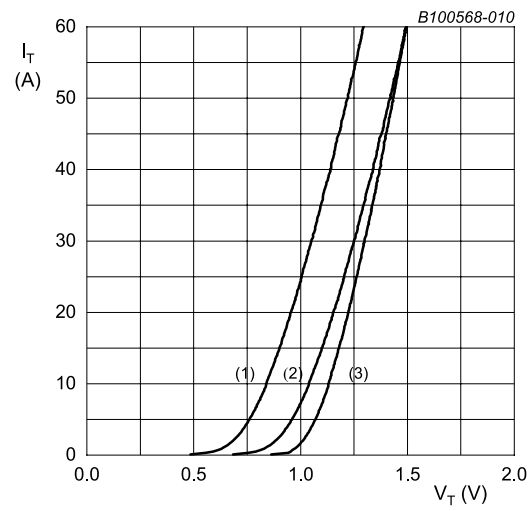


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 0.980 \text{ V}; R_s = 0.0090 \Omega$
 (1) $T_j = 150 \text{ }^\circ\text{C}$; typical values
 (2) $T_j = 150 \text{ }^\circ\text{C}$; maximum values
 (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

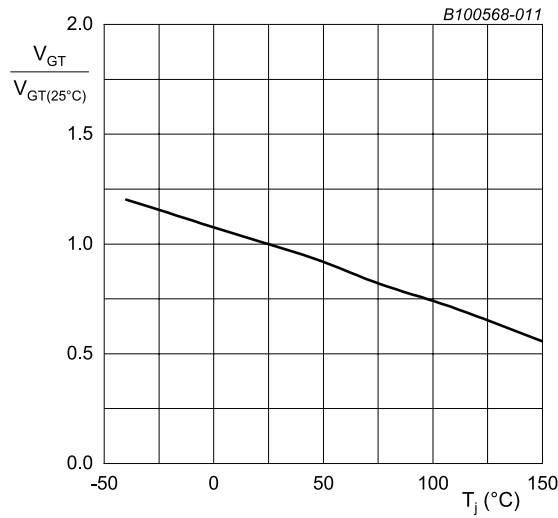
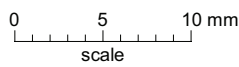
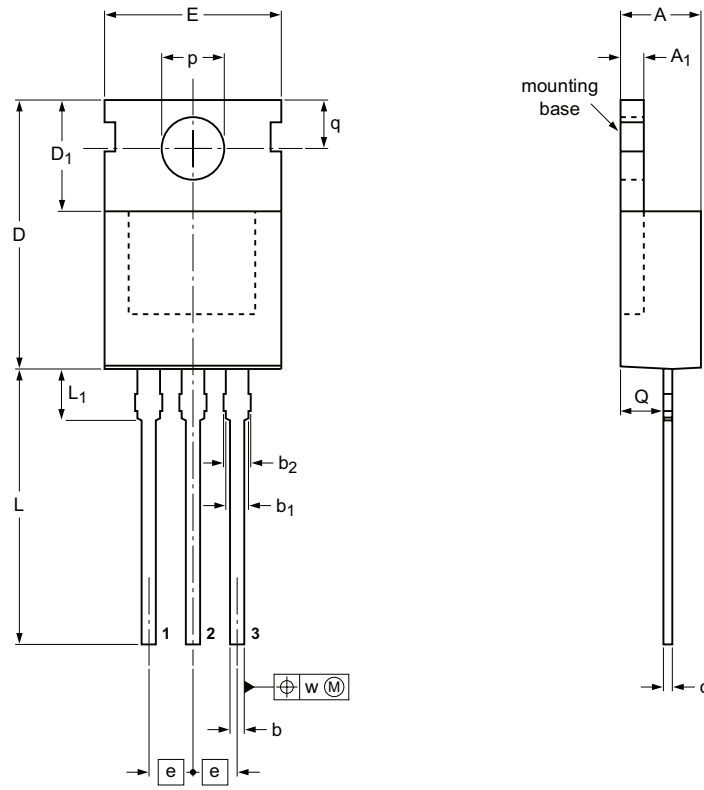


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220

SOT78D



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁	b ₂	c	D	D ₁ ref	E	e	L	L ₁ ref	p	Q	q	w
mm	4.7 4.3	1.40 1.25	0.9 0.6	1.4 1.1	1.72 1.32	0.6 0.4	16.0 15.2	6.5	10.3 9.7	2.54	14.0 12.8	3.0	3.7 3.5	2.6 2.2	3.0 2.7	0.2

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT78D		TO-220			07-04-04 07-07-10

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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